L Number	Hits	Search Text	DB	Time stamp
-	3	porous adj silicon and molecular adj switchable	USPAT; US-PGPUB; EPO; JPO;	2004/11/04 10:44
-	0	20030235927.URPN.	DERWENT USPAT	2004/10/27
-	0	6788071.URPN.	USPAT	2004/10/27
-	. 0	6713339.URPN.	USPAT	2004/10/27 16:04
_	2	porous adj silicon and nano adj2 switch	USPAT; US-PGPUB; EPO; JPO;	2004/10/27
-	7	10/304863	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/27 16:27
-	0	6806526.URPN.	USPAT	2004/10/27 16:29
_	15	(pores porous) near3 silicon and molecular adj (switch switchable)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:43
_	6	((pores porous) near3 silicon and molecular adj (switch switchable)) not (porous adj silicon and molecular adj (switch switchable))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/27 17:05
_	71	(james near3 heath).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/27 17:05
_	1	(pores porous) near3 silicon and ((james near3 heath).in.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/27 17:19
-	128	(terry near3 gilton).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 10:58
_	16	((terry near3 gilton).in.) and porous adj (Si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 10:58
_	3.	porous adj (Si semiconductor silicon) and molecular adj switchable	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 11:51
_	108	(porous adj (Si semiconductor silicon) and memory) and (phase state) near2 change	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 11:51
-	3	porous adj silicon and (catenane rotaxane pseudorotaxane)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 16:37
- ·	692	porous adj (Si semiconductor silicon) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:42
-	19	(porous adj (Si semiconductor silicon) and memory) and redox	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:42
_	107	(porous adj silicon and memory) and (phase state) near2 change	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/28 12:43

	04/10/28 2:43
	· 4 3
EPO; JPO; I	
DERWENT	
	04/10/28
manual, and (primal brane) transfer transfer transfer	: 44
EPO; JPO;	
DERWENT	
	04/10/28
	: 44
silicon and memory) and (phase state) EPO; JPO;	
near2 change) (porous adj silicon and DERWENT	
molecular adj (switch switchable))) - 20 (((pores porous) near2 (Si silicon) and USPAT; 200	004/10/20
	04/10/28 ::47
not ((porous adj silicon and memory) and EPO; JPO;	.:4/
(phase state) near2 change) DERWENT	
	04/10/28
	:04
EPO; JPO;	.04
DERWENT	
	04/10/29
	3:40
EPO; JPO;	
DERWENT	
	04/10/28
	5:58
EPO; JPO;	
DERWENT	
	04/10/28
	1:01
EPO; JPO;	
DERWENT	
- 120 (365/151).ccls. USPAT; 200	04/10/29
US-PGPUB; 10:	:49
EPO; JPO;	
DERWENT	
	04/10/29
(si silicon semiconductor semiconductive) US-PGPUB; 13:	3:19
EPO; JPO;	
DERWENT	
	04/10/29
	3:40
EPO; JPO;	
DERWENT	04/10/00
	04/10/29
	:15
EPO; JPO;	
DERWENT USPAT 200	04/10/29
	: 45
	04/11/01
	':57
EPO; JPO;	
DERWENT	
	04/11/04
	1:28
EPO; JPO;	
DERWENT	
- 64 porous adj silicon same memory USPAT; 200	04/11/04
	:44
EPO; JPO;	
DERWENT	
	04/11/04
	:44
EPO; JPO;	
DERWENT	
	04/11/04
	: 45
EPO; JPO;	
DERWENT	

-	170	(257/2).CCLS.	USPAT;	2004/11/04
		•	US-PGPUB;	14:47
			EPO; JPO;	
			DERWENT	
-	589	(257/530).CCLS.	USPAT;	2004/11/04
			US-PGPUB;	14:48
			EPO; JPO;	
İ			DERWENT	
-	378	((257/530).CCLS.) and memory	USPAT;	2004/11/04
			US-PGPUB;	14:48
ļ			EPO; JPO;	
			DERWENT	,
-	104	((257/2).CCLS.) and memory	USPAT;	2004/11/04
			US-PGPUB;	14:48
			EPO; JPO;	
			DERWENT	